IEEE WMED 2010 Technical Program

Friday, April 16th, 2010 8:00AM-7:00PM

8:00AM	Check In and Door Registration Continental Breakfast in Jordan-D
8:30AM	Welcome to WMED2010 Jordan-D Ballroom
8:45AM	Invited Talk: "CeNSE: The Central Nervous System for the Earth" Dr. Peter Hartwell, Hewlett-Packard Labs, Palo Alto Jordan-D Ballroom
9:45AM	Break & Poster Setup
10:00AM	Invited Talk: "Challenges and Innovations in Nano-CMOS Transistor Scaling" Dr. Ghani Tahir, IEEE Fellow, Intel Corporation Jordan-D Ballroom
11:00AM	Invited Talk: "Challenges and Opportunities Moving from 2D to 3D Chips" Dr. James Lu, RPI Jordan-D Ballroom
NOON	Buffet Luncheon Provided by the Workshop Jordan-AB
1:00PM	Invited Talk: "Hydrogenated Silicon (Si:H) Thin Film Solar Cells" Dr. C.R. Wronski, Penn State University. Jordan-D Ballroom
2:00PM	Invited Tutorials Tutorial A: "The title of this tutorial here", Jordan-D Dr. Banerjee Kaustav Tutorial B: "Practical Semiconductor Reliability": Jordan-C Dr. Todd Marquart, Micron Technologies (Tutorials are two hours and simultaneous)
4:00PM	Break
4:15PM	Paper Sessions Process and Devices: Jordan-D Solid State Circuits: Jordan-C (Sessions are simultaneous)
5:45PM	Poster Presentation and Reception Jordan-D Ballroom

This workshop is receiving technical co-sponsorship support from the IEEE Electron Device Society

Contributed Talks: Parallel Sessions (4:15PM-5:45PM)

Process and Devices Session

4:15p	Modified Floating Gate and IPD Profile for Better Cell Performance of Sub-50nm NAND
•	Flash Memory
	Jennifer Legun Liu, Fernando, and Y. Jeff Hu, Micron Technology, Inc., Jixin Yu, Charan
	Srinivasan, Ervin Hill, Intel Corporation
4:30p	Study of Carrier Mobility of Low-Energy, High-Dose Ion Implantations using Continuous
-	Anodic Oxidation Technique/Differential Hall Effect (CAOT/DHE) Measurements
	Shu Quin, Y. Jeff Hu, Allen Mcteer, Si Prussin, Jason Reyes, Micron Technology, Inc.
4:45p	Discrete Test Structure Device Degradation Analysis and Correlation to NAND Flash
	Circuit Operation.
	Jasper Gibbons, Puneet Sharma, Steve Porter, Jim Fulford, Praveen Vaidyanathan, Sheryll De Guzman, Pratap Murali, Micron Technology, Inc.
5:00p	A Comprehensive Study on Nanomechanical Properties of Various SiO ₂ -based Dielectric
	Films.
	Guohua Wei, Song Varghese, Kevin Beaman, Irina Vasilyeva, Tom Mendiola, Andrew Carswell, David Fillmore, and Shifeng Lu, Micron Technology, Inc.
5 :15p	A Novel Depletion Mode High Voltage Isoloation Device
•	Vladimir Mikhalev, Michael Smith, Micron Technology, Inc.
5:30p	Atomistic Study of Ultra-scaled Electron and Hole SiGe Nanowire FETs
L.	Abhijeet Paul, Saumitra Mehrotra, Methieu Luisier, Gerhard Klimeck, Purdue University
<u>Circuits S</u>	ession_
4:15p	Continuous-Time/Discrete-Time (CT/DT) Cascaded Sigma-Delta Modulator for High
	Resolution and Wideband Applications
	Ali Mesgarani, Suat U. Ay, University of Idaho, Khosrow H. Sadeghi, Sharif University of
	Technology.
4:30 p	All digital Multiplying DLL Using Precision Digital Delay Line as DCO
-	Seong-Hoon Lee, Micron Technology, Inc.

- 5:00p..... A Low Noise Low Power DC Coupled Sensor Amplifier with Offset Cancellation Hari Krishnan Krishnamurthy, Dirk Robinson, Dave M. Rector, Geroge S. La Rue, Washington State University.
- 5:15p..... Integration of a New Column-Parallel ADC Technology on CMOS Image Sensor Fan Z. Nelson, Suet U. Ay. University of Idaho
- 5:30p......Gain Error Correction for CMOS Image Sensor using Delta-Sigma Modulation Kuangming Yap, R. Jacob Baker, Boise State University

Poster Session

5:45p. Enhanced Optical Transmission in Hexagonal Plasmonic Crystals

A. English, L. Lowe, and W. Kuang, Boise State University
A Compact Delay-Locked Loop for Multi-Phase Non-Overlapping Clock Generation
Chris Gagliano and R. Jacob Baker, Boise State University
A 16-bit 500KSps Low Power SAR ADC
Kun Yang and George S. La Rue, Washington State University
Design of an On-Chip Quasi-Resonant Fixed Frequency Buck DC-DC Power Converter
Lucas A Wells, University of Idaho
Method of determination pattern placement errors (PPE) due to scanner lens aberration by
using product circuit pattern with double patterning technology
Maiko Uemura and Masato Shinohara, Micron Japan, Nishiwaki City, Hyogo, Japan
Using Gate Voltage Sensitivity to Analyze Bvdss in NAND Periphery RESURF Devices
Michael A. Smith, Micron Technology Inc

Damage Engineering of Boron-Based Low Energy Ion Implantations on USJ Fabrications Shu Qin, Y. Jeff Hu, and Allen McTeer, Micron Technology Inc.